E50A2CPS, E50A2CPR

STACK SILICON DIFFUSED DIODE

ALTERNATOR DIODE FOR AUTOMOTIVE APPLICATION.

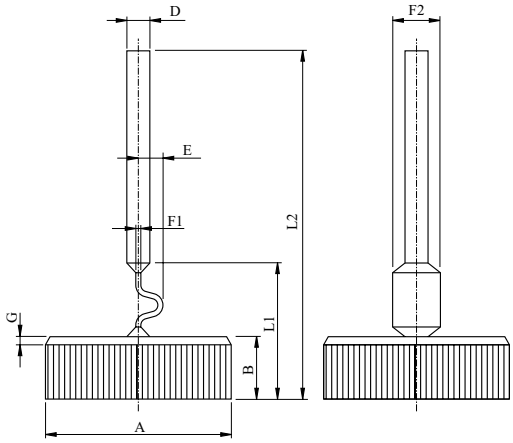
FEATURES

- Average Forward Current : I_O=50A.
- Reverse Voltage : 200V(Min.)

POLARITY

E50A2CPS (+ Type)

E50A2CPR (- Type)



DIM	MILLIMETERS	DIM	MILLIMETERS
A	Φ11.7+0.1/-0	F1	0.32
B	3.85+0/-0.2	F2	3.1
D	Φ1.45± 0.1	G	0.5
E	1.55	L1	8.4 MAX

DIM	TYPE	POLARITY	MILLIMETERS
L2	S	▼	17.5+0/-1.5
	R	▲	21.5+0/-1.5

H-PF

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Average Forward Current	$I_{F(AV)}$	50	A
Peak 1 Cycle Surge Current	I_{FS}	500 (60Hz)	A
Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Junction Temperature	T_j	-40 200	℃
Storage Temperature Range	T_{stg}	-40 200	℃

Not recommended for new design

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	I_{FM}=100A	-	-	1.05	V
Reverse Voltage	V_R	I_R=5mA	200	-	-	V
Reverse Current	I_R	V_R=200V	-	-	50	μA
Transient Thermal Resistance	ΔV_F	I_{FM}=100A, I_M=100mA, Pw=100ms	-	-	130	mV
Reverse Recovery Time	t_{rr}	I_F=100mA, I_{RP}=100mA	-	-	15	μs
Reverse Leakage Current Under High Temperature	HI_R	Ta=150℃, V_R=200V	-	-	2.5	mA
Temperature Resistance	R_{th}	Junction to Base	-	-	0.8	℃/W
		Junction to Fin	-	-	1.0	